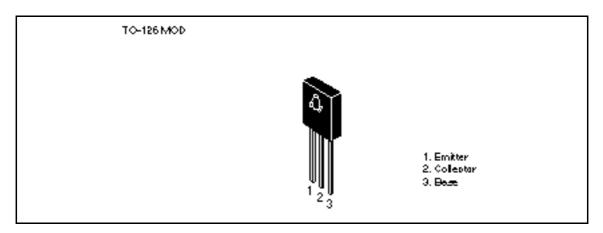
Silicon NPN Epitaxial

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Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

		Ratings			
Item	Symbol	2SC1212	2SC1212A	Unit	
Collector to base voltage	V _{CBO}	50	80	V	
Collector to emitter voltage	V _{CEO}	50	80	V	
Emitter to base voltage	V _{EBO}	4	4	V	
Collector current	Ι _c	1	1	А	
Collector power dissipation	Pc	0.75	0.75	W	
	Pc*1	8	8	W	
Junction temperature	Tj	150	150	°C	
Storage temperature	Tstg	-55 to +150	-55 to +150	°C	

Note: 1. Value at $T_c = 25^{\circ}C$



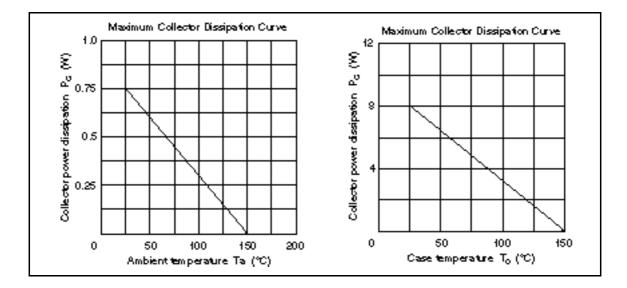
Electrical Characteristics (Ta = 25°C)

		2SC1	212		2SC1212A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	50	—	—	80	—	_	V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	50	—	—	80	—	_	V	$I_c = 10 \text{ mA}, \text{ R}_{\text{BE}} =$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	4	_	_	4	_	_	V	$I_{\rm E} = 1$ mA, $I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	5	_	—	5	μA	$V_{CB} = 50 \text{ V}, \ I_{E} = 0$
DC current tarnsfer ratio	h_{FE}^{*1}	60	_	200	60	_	200		V_{ce} = 4 V, I_c = 50 mA
	h _{FE}	20	_	_	20	_	_		$V_{CE} = 4 V, I_{C} = 1 A$ (pulse test)
Base to emitter voltage	V_{BE}	_	0.65	1.0	_	0.65	1.0	V	V_{ce} = 4 V, I_c = 50 mA
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	0.75	1.5	—	0.75	1.5	V	$I_{c} = 1 \text{ A}, I_{B} = 0.1 \text{ A}$ (pulse test)
Gain bandwidth product	f _T		160		_	160	_	MHz	V_{ce} = 4 V, I_c = 30 mA

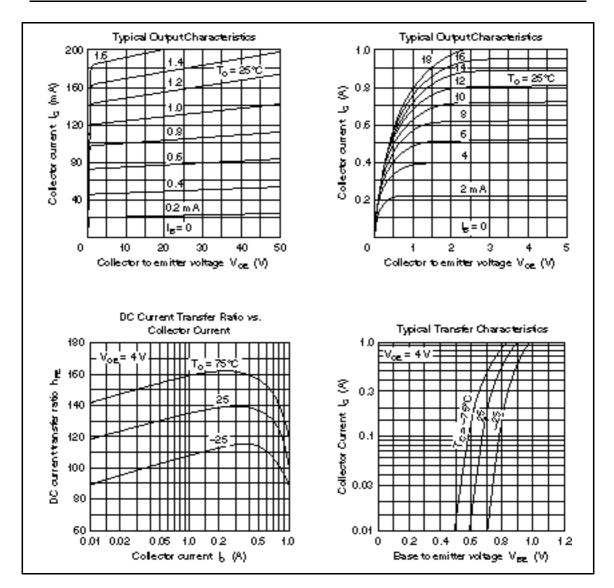
Note: 1. The 2SC1212 and 2SC1212A are grouped by $h_{\mbox{\tiny FE}}$ as follows.

в с

60 to 120 100 to 200



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